CoolMOS® Power Transistor

Features

- Lowest figure-of-merit R_{ON} x Q_g
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified for industrial grade applications according to JEDEC[1)]
- Pb-free lead plating; RoHS compliant;
  available in Halogen free mold compound[a)]

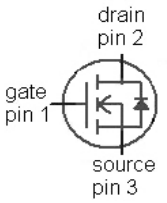
CoolMOS CP is designed for:

- Hard switching SMPS topologies

Product Summary

V_{DS} @ $T_{j,max}$	650	V
$R_{DS(on),max}$ @ T_j =25°C	0.6	Ω
$Q_{g,typ}$	21	nC

PG-TO252



Type	Package	Marking
IPD60R600CP	PG-TO252	6R600P

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C	6.1	A
		T_C=100 °C	3.8	
Pulsed drain current[2)]	$I_{D,pulse}$	T_C=25 °C	15	
Avalanche energy, single pulse	E_{AS}	I_D=2.2 A, V_{DD}=50 V	144	mJ
Avalanche energy, repetitive t_{AR}[2),3)]	E_{AR}	I_D=2.2 A, V_{DD}=50 V	0.2	
Avalanche current, repetitive t_{AR}[2),3)]	I_{AR}		2.2	A
MOSFET dv/dt ruggedness	dv/dt	V_{DS}=0...480 V	50	V/ns
Gate source voltage	V_{GS}	static	±20	V
		AC (f>1 Hz)	±30	
Power dissipation	P_{tot}	T_C=25 °C	60	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C

[a)] non-Halogen free (OPN: IPD60R600CPBT); Halogen free (OPN: IPD60R600CPAT)

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	T_C=25 °C	3.3	A
Diode pulse current[2]	$I_{S,pulse}$		15	
Reverse diode dv/dt[4]	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	2.1	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
	R_{thJA}	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm^2 cooling area[3]	-	35	-	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=220µA	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600 V, V_{GS}=0 V, T_j=25 °C	-	-	1	µA
		V_{DS}=600 V, V_{GS}=0 V, T_j=150 °C	-	10	-	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=3.3 A, T_j=25 °C	-	0.54	0.6	Ω
		V_{GS}=10 V, I_D=3.3 A, T_j=150 °C	-	1.5	-	
Gate resistance	R_G	f=1 MHz, open drain	-	1.5	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=100 V, f=1 MHz	-	550	-	pF
Output capacitance	C_{oss}		-	28	-	
Effective output capacitance, energy related[5]	$C_{o(er)}$	V_{GS}=0 V, V_{DS}=0 V to 480 V	-	26	-	
Effective output capacitance, time related[6]	$C_{o(tr)}$		-	67	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=400 V, V_{GS}=10 V, I_D=3.3 A, R_G=23.1 Ω	-	17	-	ns
Rise time	t_r		-	12	-	
Turn-off delay time	$t_{d(off)}$		-	75	-	
Fall time	t_f		-	17	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480 V, I_D=3.3 A, V_{GS}=0 to 10 V	-	2	-	nC
Gate to drain charge	Q_{gd}		-	10	-	
Gate charge total	Q_g		-	21	27	
Gate plateau voltage	$V_{plateau}$		-	4.7	-	V
Reverse Diode						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=3.3 A, T_j=25 °C	-	0.8	1.2	V
Reverse recovery time	t_{rr}	V_R=400 V, I_F=I_S, di_F/dt=100 A/µs	-	220	-	ns
Reverse recovery charge	Q_{rr}		-	2.3	-	µC
Peak reverse recovery current	I_{rrm}		-	18	-	A

[1] J-STD20 and JESD22

[2] Pulse width t_p limited by $T_{j,max}$

[3] Repetitive avalanche causes additional power losses that can be calculated as P_{AV}=E_{AR}*f.

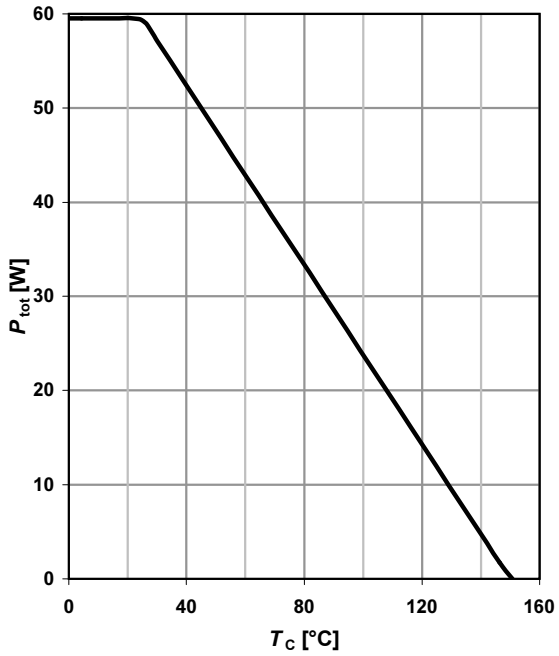
[4] I_{SD}=I_D, di/dt≤400A/µs, V_{DClink}=400V, V_{peak}<$V_{(BR)DSS}$, T_j<T_{jmax}, identical low side and high side switch

[5] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[6] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

1 Power dissipation

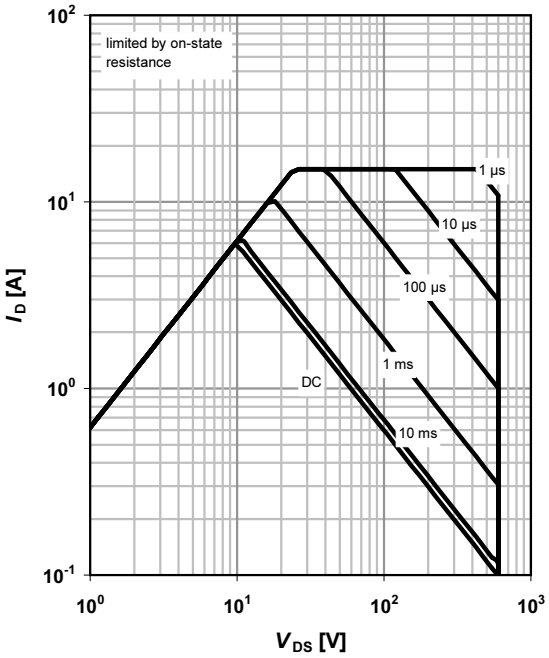
$P_{tot}=f(T_C)$



2 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

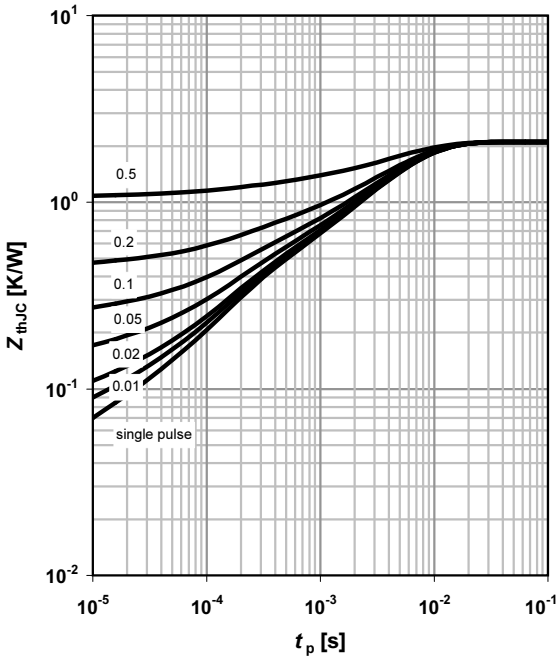
parameter: t_p



3 Max. transient thermal impedance

$Z_{thJC}=f(t_P)$

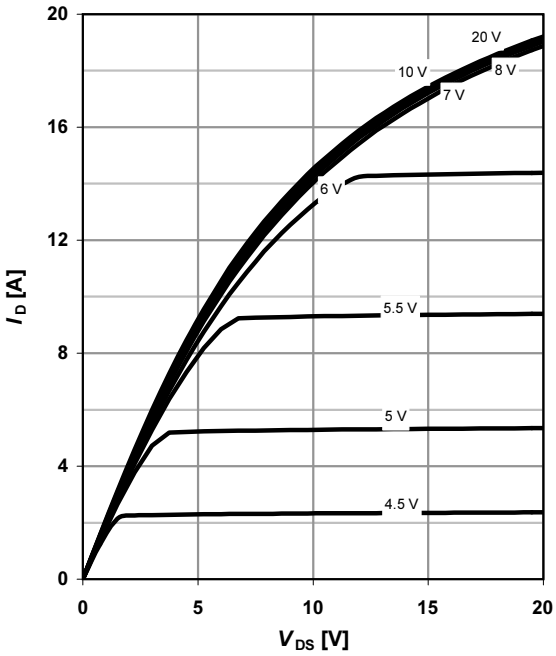
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C

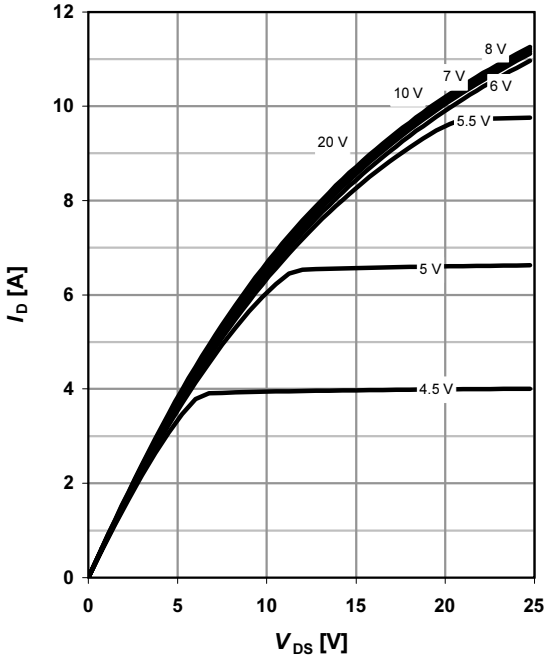
parameter: V_{GS}



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=150 °C

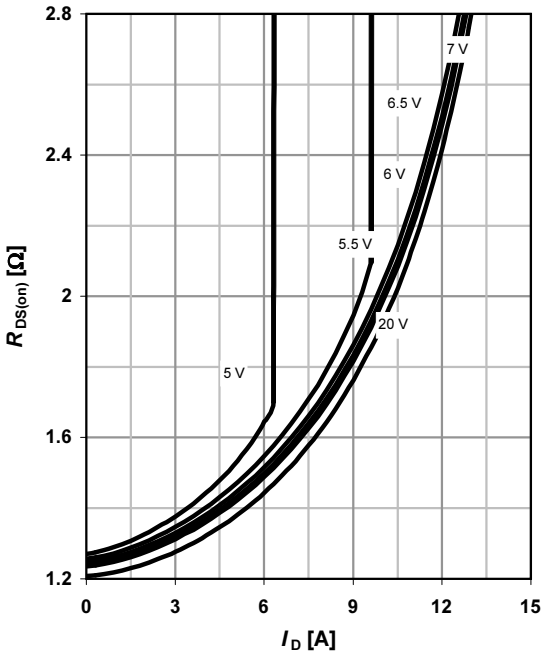
parameter: V_{GS}



6 Typ. drain-source on-state resistance

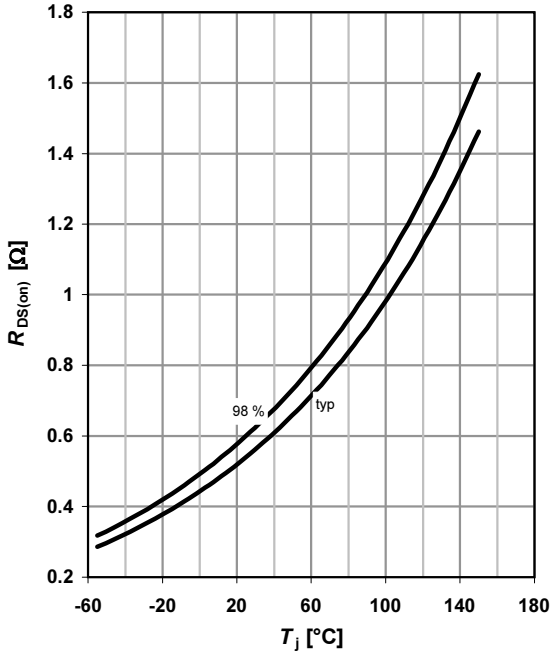
$R_{DS(on)}$=f(I_D); T_j=150 °C

parameter: V_{GS}



7 Drain-source on-state resistance

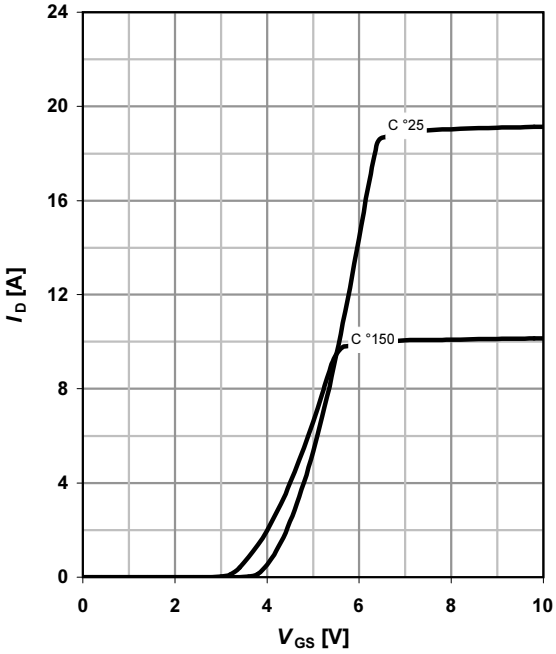
$R_{DS(on)}$=f(T_j); I_D=3.3 A; V_{GS}=10 V



8 Typ. transfer characteristics

I_D=f(V_{GS}); |V_{DS}|>2|I_D|$R_{DS(on)max}$

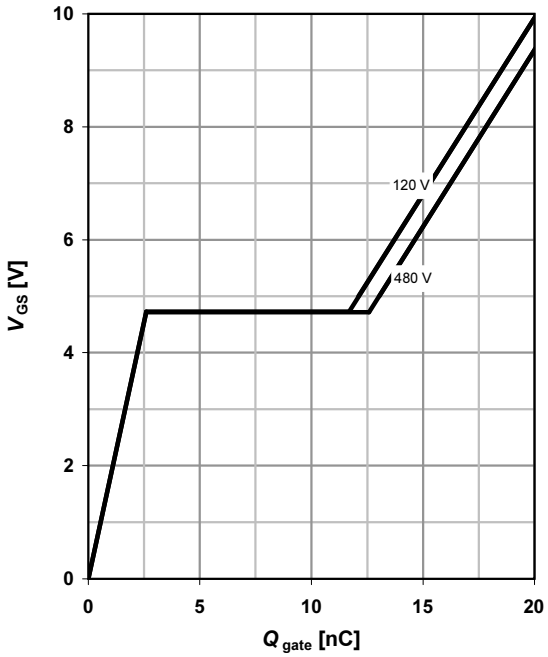
parameter: T_j



9 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=3.3 A pulsed

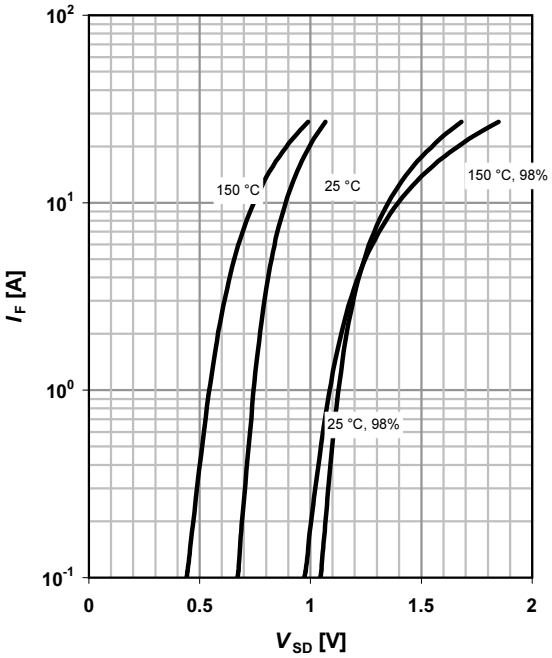
parameter: V_{DD}



10 Forward characteristics of reverse diode

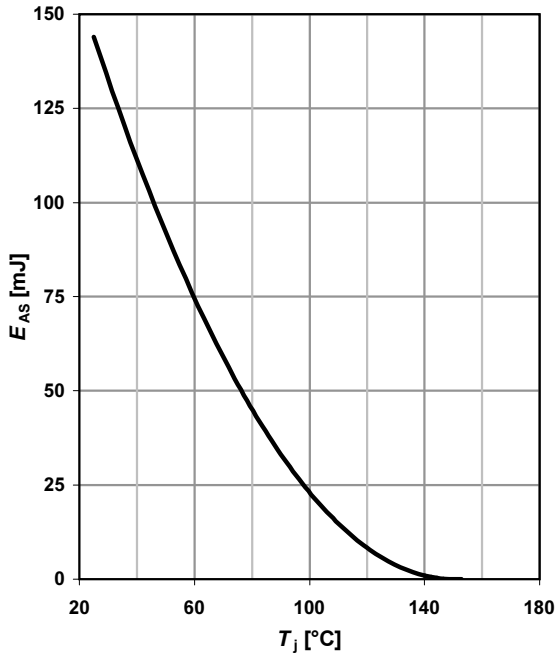
I_F=f(V_{SD})

parameter: T_j



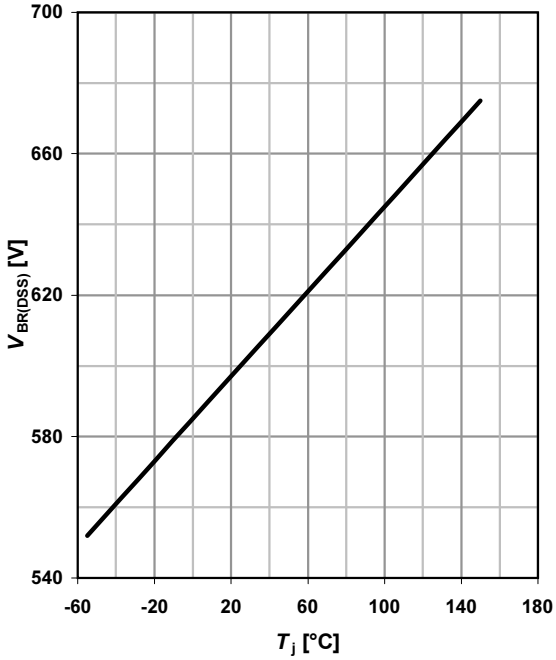
11 Avalanche energy

E_{AS}=f(T_j); I_D=2.2 A; V_{DD}=50 V



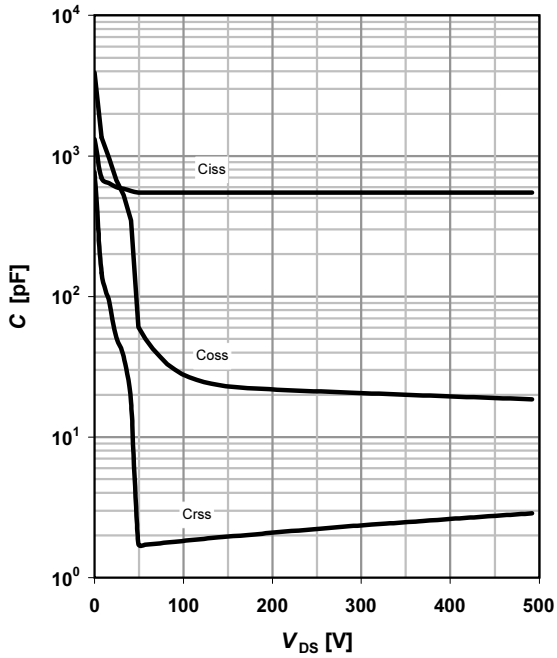
12 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=0.25 mA



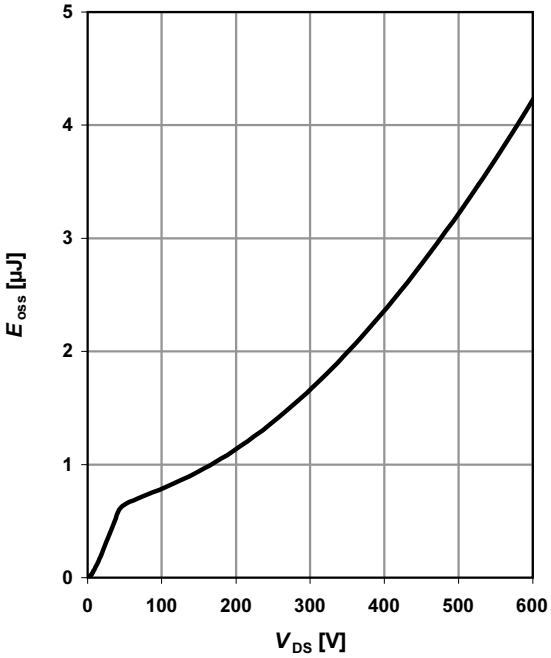
13 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

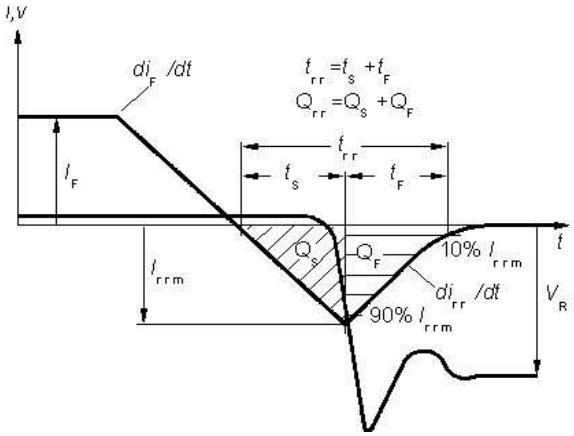


14 Typ. Coss stored energy

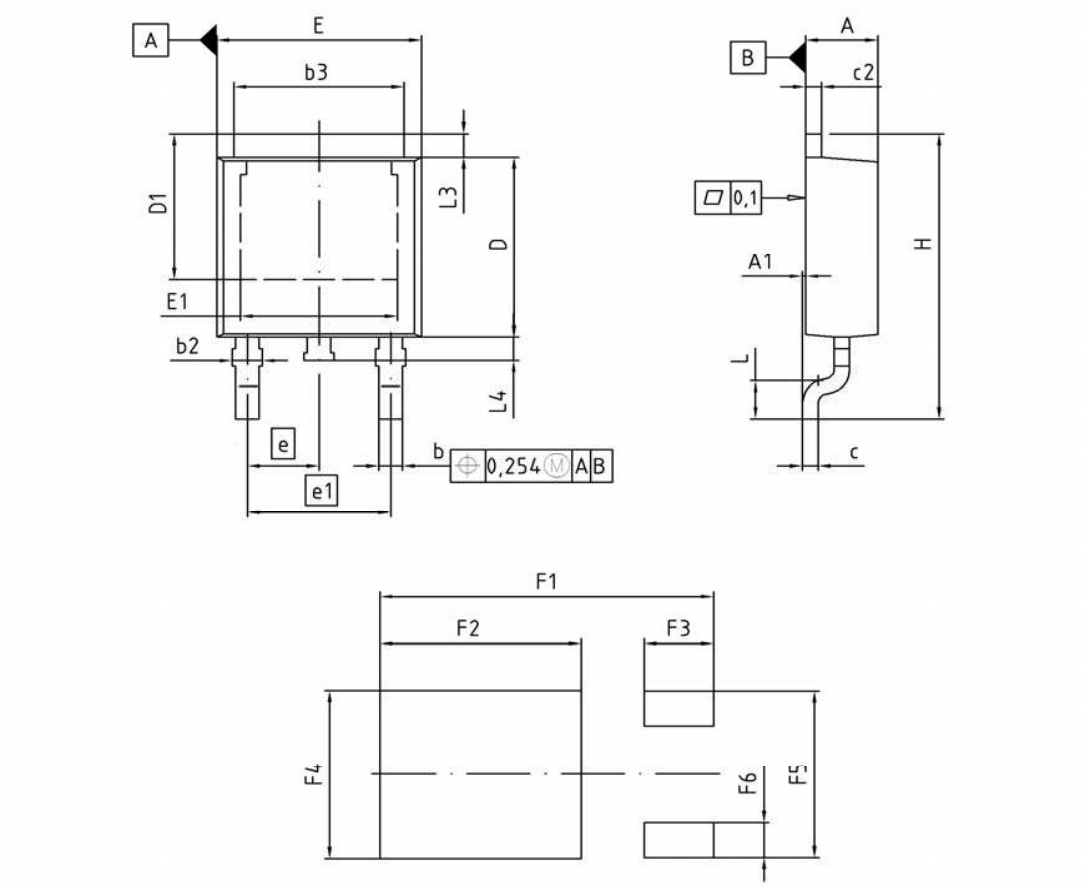
E_{oss}= f(V_{DS})



Definition of diode switching characteristics



PG-TO252: Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

DOCUMENT NO.
Z8B00003328

SCALE 0 2.0 0 2.0 4mm

EUROPEAN PROJECTION

ISSUE DATE
19-10-2007

REVISION
03

Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer
The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information
For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings
Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.